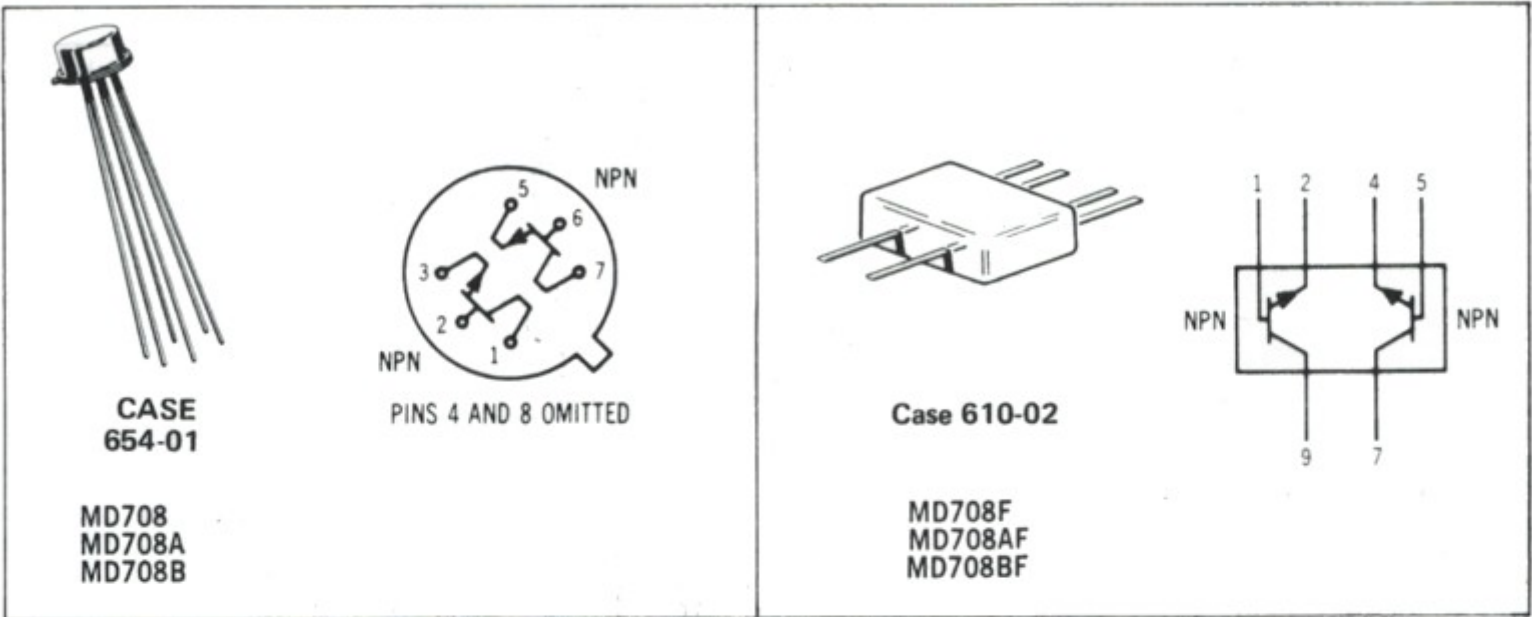


MD708, F (SILICON)
MD708A, F
MD708B, F

Dual NPN silicon annular transistors designed for high-speed, logic switching and space saving considerations. Matched pairs are available for differential amplifier applications.



Pin Connections, Bottom View
All Leads Electrically Isolated from Case

MAXIMUM RATINGS (each side) (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V _{CEO}	15		Vdc
Collector-Base Voltage	V _{CB}	40		Vdc
Emitter-Base Voltage	V _{EB}	5.0		Vdc
Collector Current	I _C	200		mAdc
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200		°C
Total Device Dissipation @ T _A = 25°C	P _D	One Side	Both Sides	mW
		300	400	mW/°C
		1.7	2.3	
Flat Package Derate above 25°C		250	350	mW
		1.5	2.0	mW/°C

FIGURE 1 — TURN-ON AND TURN-OFF TIME TEST CIRCUIT

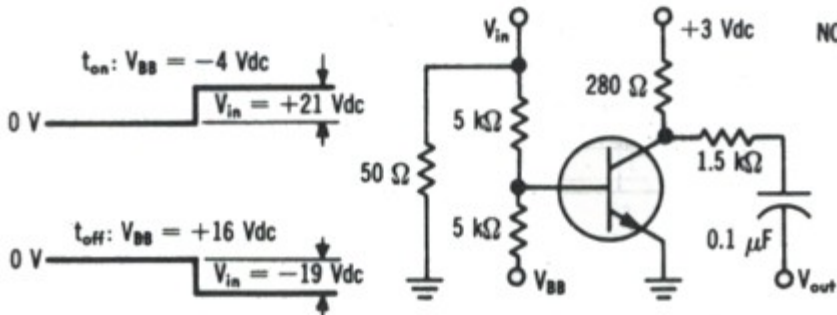
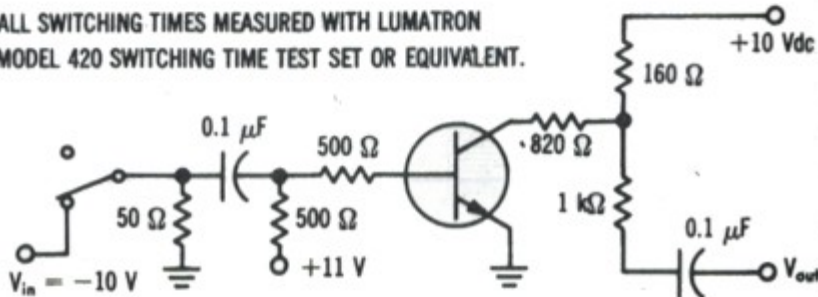


FIGURE 2 — CHARGE-STORAGE TIME CONSTANT TEST CIRCUIT

NOTE: ALL SWITCHING TIMES MEASURED WITH LUMATRON MODEL 420 SWITCHING TIME TEST SET OR EQUIVALENT.



MD708,F/MD708A,F/MD708B,F (continued)**ELECTRICAL CHARACTERISTICS** (each side) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) ($I_C = 30\text{ mAdc}$, $I_B = 0$)	$BV_{CEO(sus)}$	15	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $I_E = 0$)	BV_{CBO}	40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	BV_{EBO}	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $T_A = +150^\circ\text{C}$)	I_{CBO}	— —	0.015 50	μAdc
ON CHARACTERISTICS				
DC Current Gain (1) ($I_C = 0.5\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 150\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	40 40 35 30	— 200 — —	—
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	— — —	0.2 0.35 0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 10\text{ mAdc}$, $I_B = 1\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{BE(sat)}$	0.65 — —	0.85 0.95 1.1	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain-Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 100\text{ kHz}$)	C_{ob}	—	5.0	pF
Input Capacitance ($V_{BE} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 100\text{ kHz}$)	C_{ib}	—	7.0	pF
Charge-Storage Time Constant (Figure 2) ($I_C = 10\text{ mAdc}$, $I_{B1} = I_{B2} = 10\text{ mAdc}$)	t_s	—	25	ns
Turn-On Time (Figure 1) ($I_C = 10\text{ mAdc}$, $I_{B1} = 3\text{ mAdc}$, $I_{B2} = 1\text{ mAdc}$)	t_{on}	—	35	ns
Turn-Off Time (Figure 1) ($I_C = 10\text{ mAdc}$, $I_{B1} = 3\text{ mAdc}$, $I_{B2} = 1\text{ mAdc}$)	t_{off}	—	75	ns
MATCHING CHARACTERISTICS				
DC Current Gain Ratio** ($I_C = 10\text{ mAdc}$, $V_{CE} = 1\text{ Vdc}$)	MD708A, MD708AF MD708B, MD708BF h_{FE1}/h_{FE2}^{**}	0.9 0.8	1.0 1.0	—
Base Voltage Differential ($I_C = 10\text{ mAdc}$, $V_{CE} = 1\text{ Vdc}$)	MD708A, MD708AF MD708B, MD708BF $ V_{BE1} - V_{BE2} $	— —	5.0 10	mVdc
Base Voltage Differential Gradient ($I_C = 10\text{ mAdc}$, $V_{CE} = 1\text{ Vdc}$, $T_A = -55$ to $+125^\circ\text{C}$)	MD708A, MD708AF MD708B, MD708BF $\frac{\Delta(V_{BE1} - V_{BE2})}{\Delta T_A}$	— —	10 20	$\mu\text{V}/^\circ\text{C}$

(1) Pulse Test: Pulse Width = 300 μs ; Duty Cycle = 2%**The lowest h_{FE} reading is taken as h_{FE1} for this test.